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ATTY DOCKET NO. 3308 CON

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

4/3/13

IN THE APPLICATION OF:)

BIN-SHING CHEN)

Group Art Unit 2811

SERIAL NO.: (Continuation of 09/769,576))

Examiner Thien F. Tran

FILED:)

FOR: METHOD FOR MANUFACTURING)
SPLIT-GATE EEPROM MEMORY)
CELL AND STRUCTURE FORMED)
THEREBY)PRELIMINARY AMENDMENTThe Honorable Commissioner of
Patents and Trademarks
Washington, D. C. 20231

Sir:

RECEIVED
MAR 31 2003
TECHNOLOGY CENTER 2800

This application is a continuation application of prior application U.S. Serial No. 09/769,586

In the Claims:

Please cancel claims 1-10, amend Claim 11, and add new Claim 12 as follows:

SUB C17 11. (Once Amended) A structure of an Electrically Erasable Programmable Read-Only
Memory (EEPROM), comprising:

a silicon substrate having a source/drain region;

a tunnel oxide layer disposed over said silicone substrate;

a select gate disposed over said tunnel oxide layer, wherein said select gate is defined
by a conductive layer covered with a first insulated material thereon and comprises a sidewall made
of a second insulated material;a sidewall forming a single floating gate aligned to one side of said select gate;